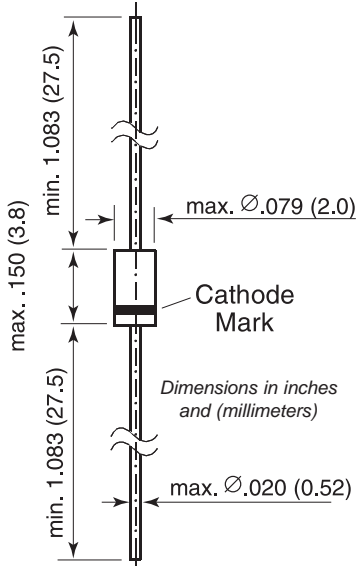


Small-Signal Diode

Reverse Voltage 100V
Forward Current 150mA**DO-204AH (DO-35 Glass)**

Features

- Silicon Epitaxial Planar Diode
- Fast switching diode

Mechanical Data

Case: DO-35 Glass Case**Weight:** approx. 0.13g**Packaging Codes/Options:**F2/10K per Ammo tape (52mm), 50K/box
F3/10K per 13" reel (52mm tape), 50K/box

Maximum Ratings and Thermal Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Reverse voltage	V_R	75	V
Peak reverse voltage	V_{RM}	100	V
Maximum average rectified current half wave rectification with resistive load at $T_{amb} = 25^\circ\text{C}$ and $f \geq 50\text{Hz}^{(1)}$	$I_{F(AV)}$	150	mA
Surge forward current at $t < 1\text{s}$ and $T_j = 25^\circ\text{C}$	I_{FSM}	500	mA
Maximum power dissipation at $T_{amb} = 25^\circ\text{C}^{(1)}$	P_{tot}	500	mW
Thermal resistance junction to ambient air ⁽¹⁾	$R_{\theta JA}$	350	$^\circ\text{C/W}$
Maximum junction temperature	T_J	175	$^\circ\text{C}$
Storage temperature range	T_S	-65 to +175	$^\circ\text{C}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Min.	Max.	Unit
Maximum forward voltage drop at $I_F = 10\text{mA}$	V_F	-	1.0	V
Leakage current at $V_R = 50\text{V}$ at $V_R = 75\text{V}$	I_R	-	100 5	nA μA
Reverse breakdown voltage tested with 100 μA pulses	$V_{(BR)R}$	100	-	V
Capacitance at $V_F = V_R = 0\text{V}$	C_{tot}	-	2	pF
Reverse recovery time from $I_F = 10\text{mA}$ to $I_R = 1\text{mA}$, $V_R = 6\text{V}$, $R_L = 100\Omega$	t_{rr}	-	4	ns
Rectification efficiency at $f = 100\text{MHz}$, $V_{RF} = 2\text{V}$	η_v	0.45	-	-

Note:

(1) Valid provided that leads at a distance of 8mm from case are kept at ambient temperature

Ratings and Characteristic Curves ($T_A = 25^\circ\text{C}$ unless otherwise noted)

